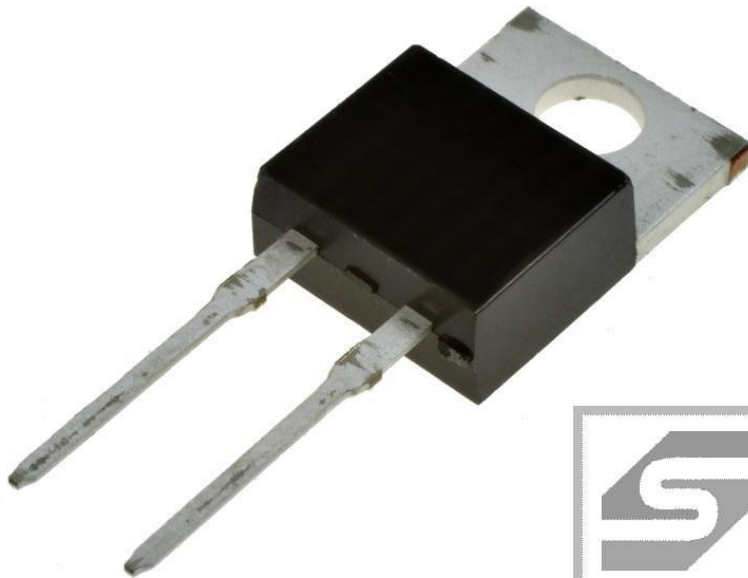




Dioda FES8JT GI TO220AC 8A;600V;50ns



Dane techniczne:

Nazwa: FES8JT

Typ: dioda szybka

Napięcie wsteczne maksymalne: 600V

Napięcie przewodzenia maksymalne: 1,5V

Prąd przewodzenia: 8A

Prąd w impulsie maksymalny: 125A

Czas gotowości: 50ns

Pojemność: 50pF

Prąd upływu 500μA

Obudowa: TO220AC

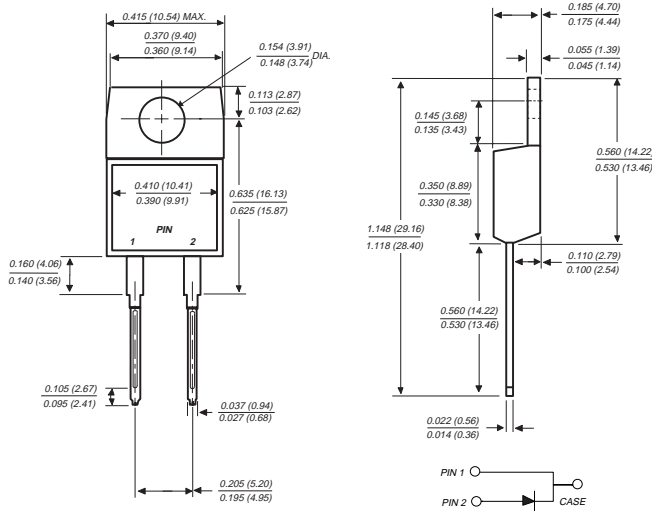
Montaż: przewlekany(THT)

FES8AT THRU FES8JT

FAST EFFICIENT PLASTIC RECTIFIER

Reverse Voltage - 50 to 600 Volts Forward Current - 8.0 Amperes

TO-220AC



Dimensions in inches and (millimeters)

FEATURES

- ◆ Plastic package has Underwriters Laboratory Flammability Classification 94V-0
- ◆ Glass passivated chip junction
- ◆ Low leakage, high voltage
- ◆ High surge current capability
- ◆ Superfast recovery time, for high efficiency
- ◆ High temperature soldering guaranteed: 250°C, 0.16" (4.06mm) from case for 10 seconds



MECHANICAL DATA

Case: JEDEC TO-220AC fully overmolded plastic body over passivated chip

Terminals: Plated lead solderable per MIL-STD-750, Method 2026

Polarity: As marked

Mounting Position: Any

Mounting Torque: 5 in. - lbs. max.

Weight: 0.064 ounce, 1.81 grams

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

	SYMBOLS	FES 8AT	FES 8BT	FES 8CT	FES 8DT	FES 8FT	FES 8GT	FES 8HT	FES 8JT	UNITS
Maximum recurrent peak reverse voltage	V _{RRM}	50	100	150	200	300	400	500	600	Volts
Maximum RMS voltage	V _{RMS}	35	70	105	140	210	280	350	420	Volts
Maximum DC blocking voltage	V _{DC}	50	100	150	200	300	400	500	600	Volts
Maximum average forward rectified current at T _C =100°C	I _(AV)	8.0								Amps
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	125.0								Amps
Maximum instantaneous forward voltage at 8.0A	V _F	0.95			1.3		1.5		Volts	
Maximum DC reverse current at rated DC blocking voltage	I _R	10.0				500.0				μA
		at T _C =25°C				at T _C =100°C				
Maximum reverse recovery time (NOTE 1)	t _{rr}	35.0			50.0			ns		
Typical junction capacitance (NOTE 2)	C _J	85.0					60.0			pF
Typical thermal resistance (NOTE 3)	R _{θJA}	15.0								°C/W
(NOTE 4)	R _{θJC}	2.2								
Operating junction and storage temperature range	T _J , T _{STG}	-65 to +150								°C

NOTES:

- (1) Reverse recovery test conditions: I_F=0.5A, I_R=1.0A, I_{rr}=0.25A
- (2) Measured at 1.0 MHz and applied reverse voltage of 4.0 Volts
- (3) Thermal resistance from junction to ambient in free air, no heatsink
- (4) Thermal resistance from junction to case mounted on heatsink

RATINGS AND CHARACTERISTIC CURVES FES8AT THRU FES8JT

FIG. 1 - MAXIMUM FORWARD CURRENT DERATING CURVES

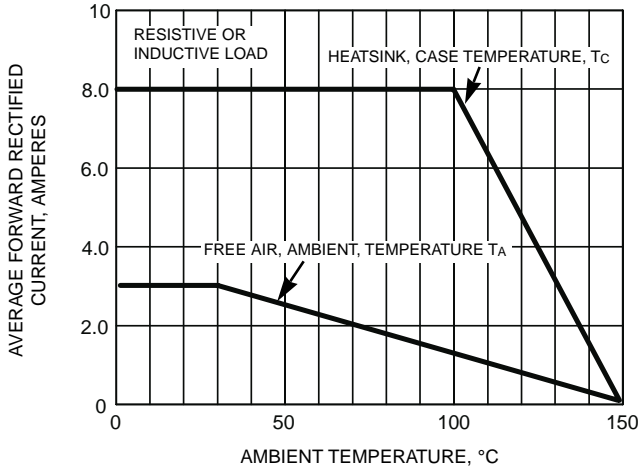


FIG. 2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

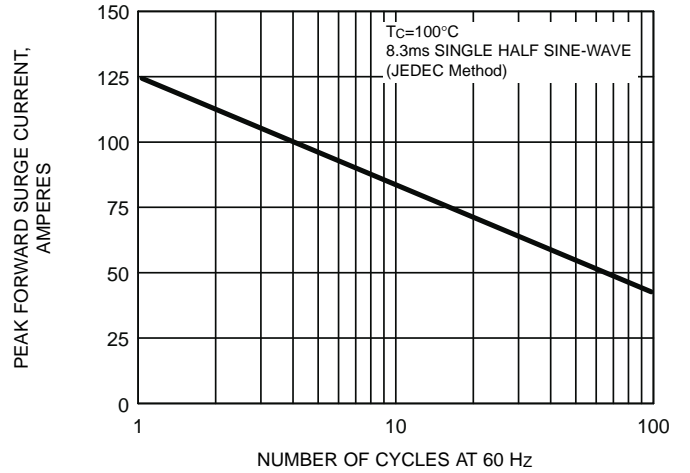


FIG. 3 - TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

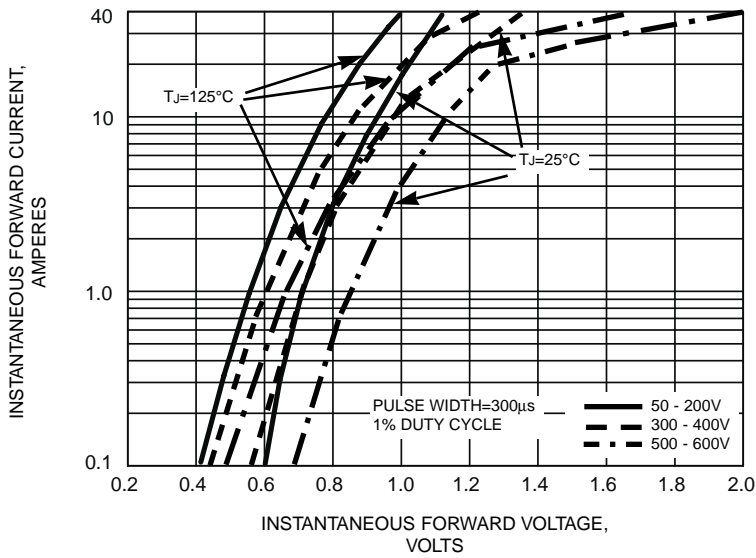


FIG. 4 - TYPICAL REVERSE LEAKAGE CHARACTERISTICS

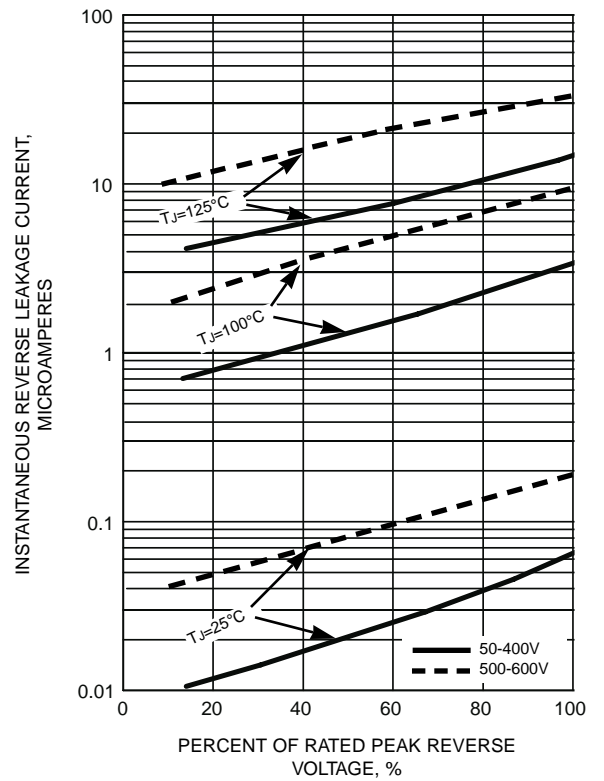
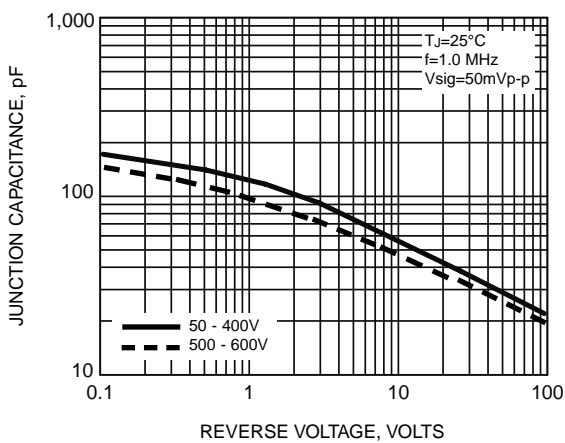


FIG. 5 - TYPICAL JUNCTION CAPACITANCE



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Datasheets for electronics components.